

**Amendments to the Specification:**

Please replace paragraph [0005] with the following amended paragraph:

[0005] However, the semiconductor film thus crystallized using the pulsed laser light includes a plurality of crystal grains assembled and the position and the size of the crystal grain are random. Compared to an inside of the crystal grain, a boundary between the crystal grains (crystal grain boundary) has an amorphous structure and an infinite number of recombination centers and trapping centers existing due to a crystal defect or the like. There is a problem that when a carrier is trapped in the trapping center, potential of the crystal grain boundary increases to become a barrier against the carrier, and thereby lowering a ~~current~~ transporting characteristic of the carrier.

Please replace paragraph [0158] with the following amended paragraph:

[0158] And the concentration of the catalyst element in the rest of the regions in the semiconductor film 531 can be decreased to  $1 \times 10^{17}$  ~~[[atms]]~~ atoms/cm<sup>3</sup> or less by removing the region 533 with phosphorous added by means of etching. After removing the silicon oxide film 532 for the mask, the semiconductor film 531 is patterned to form island-shaped semiconductor films 534 to 536. (FIG. 11(D)) With the island-shaped semiconductor films 534 to 536, it is possible to form various kinds of semiconductor elements typified by TFT. It is noted that the gettering process in the present invention is not limited to the method shown in this embodiment. The other method may be also employed in order to decrease the catalyst element in the semiconductor film.